

DW_ram_2r_w_s_lat

Sync. Write-Port, Async. Dual Read-Port RAM (Latch-Based)

Version, STAR and Download Information: IP Directory

Features and Benefits

- Parameterized word depth
- Parameterized data width
- Synchronous static memory

Description

DW_ram_2r_w_s_lat implements a parameterized, synchronous, three-port static RAM consisting of one write port and two read ports. The RAM can perform simultaneous read and write operations.

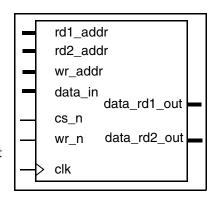


Table 1-1 Pin Description

Pin Name	Width	Direction	Function
clk	1 bit	Input	Clock
cs_n	1 bit	Input	Chip select, active low
wr_n	1 bit	Input	Write enable, active low
rd1_addr	ceil(log ₂ [depth]) bit	Input	Read1 address bus
rd2_addr	ceil(log ₂ [depth]) bit(s)	Input	Read2 address bus
wr_addr	ceil(log ₂ [depth]) bit(s)	Input	Write address bus
data_in	data_width bit(s)	Input	Input data bus
data_rd1_out	data_width bit(s)	Output	Output data bus for read1
data_rd2_out	data_width bit(s)	Output	Output data bus for read2

Table 1-2 Parameter Description

Parameter	Values	Description
data_width	1 to 256 Default = none	Width of data_in and data_out buses
depth	2 to 256 Default = none	Number of words in the memory array (address width)

Table 1-3 Synthesis Implementations

Implementation Name	Function	License Feature Required
str	Synthesis model	DesignWare

Table 1-4 Simulation Models

Model	Function
DW06.DW_RAM_2R_W_S_LAT_CFG_SIM	VHDL simulation configuration
dw/dw06/src/DW_ram_2r_w_s_lat_sim.vhd	VHDL simulation model source code
dw/sim_ver/DW_ram_2r_w_s_lat.v	Verilog simulation model source code

Write data enters the RAM through the data_in input port, and is read through either the data_rd1_out port or the data_rd2_out port. The RAM is constantly reading regardless of the state of cs_n.

The rd1_addr, rd2_addr, and wr_addr ports are used to address the *depth* words in the memory. If rd1_addr or rd2_addr contains a value beyond the maximum *depth* value, that corresponding output port is driven LOW. For example, if rd1_addr = 7 and depth = 6, then the data_rd1_out bus is driven LOW. If rd2_addr is beyond the maximum depth, then data_rd2_out is driven LOW.

For wr_addr beyond the maximum depth (for example, wr_addr = 7 and depth = 6), nothing occurs and the data is lost. No warnings are given during simulations when an address beyond the scope of depth is used.



This component contains enable signals for internal latches that are derived from the wr_n port. To keep hold times to a minimum, you should consider instances of this component to be individual floorplanning elements.

Chip Selection, Reading and Writing

The cs_n input is the chip select, active low signal that enables data to be written to the RAM. The RAM is constantly reading, regardless of the state of cs_n.

When cs_n, wr_n (write enable, active low), and clk are LOW, data_in is transparent to the internal memory cell being accessed by wr_addr (data_in = output data of the memory cell). Therefore, during the period when clk is LOW, a change in data in is reflected on the output of the internal memory cell being accessed. If one of the read address buses is the same value as wr_addr and wr_n is LOW, data_in equals the output data when clk is LOW. Data is captured into the memory cell on the rising edge of clk.

When cs_n is HIGH, writing to the RAM is disabled.

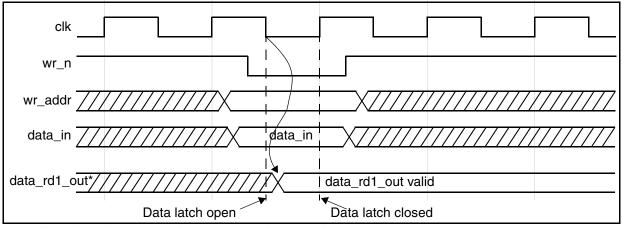
Application Notes

DW_ram_2r_w_s_lat is intended to be used as small scratch-pad memory, programmable lookup tables, and writable control storage. Because DW_ram_2r_w_s_lat is built from the cells within the ASIC cell library, it should be kept small to obtain an efficient implementation. If a larger memory is required, you should consider using a hard macro RAM from the ASIC library in use.

Timing Waveforms

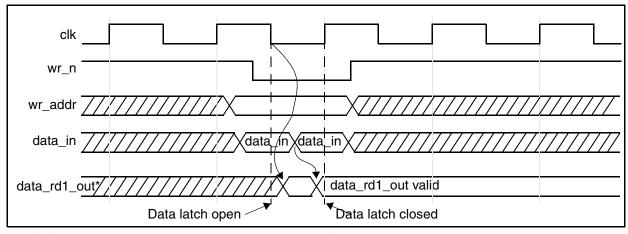
Figure 1-1 Instantiated RAM Timing Waveforms

Write Timing, cs_n = 0, Normal Data Input and Output



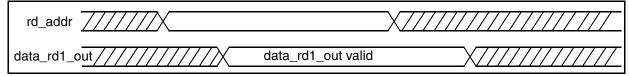
^{*} Write through is seen only when rd_addr = wr_addr.

Write Timing, cs_n = 0, Changing Data Input and Output

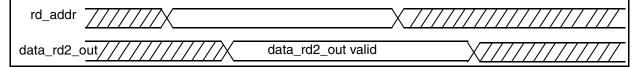


^{*} Write through is seen only when rd_addr = wr_addr.

Read Port 1 Timing, address controlled, cs_n = don't care



Read Port 2 Timing, address controlled, cs_n = don't care



Related Topics

- Memory Synchronous RAMs Listing
- DesignWare Building Block IP Documentation Overview

HDL Usage Through Component Instantiation - VHDL

```
library IEEE, DWARE, DWARE;
use IEEE.std_logic_1164.all;
use DWARE.DWpackages.all;
use DWARE.DW foundation comp.all;
entity DW ram 2r w s lat inst is
  generic (inst_data_width : INTEGER := 8; inst_depth : INTEGER := 8 );
  port (inst_clk : in std_logic;
        inst cs n
                    : in std logic;
        inst wr n : in std logic;
       inst_rd1_addr : in std_logic_vector(bit_width(inst_depth)-1 downto 0);
       inst rd2 addr : in std logic vector(bit width(inst depth)-1 downto 0);
        inst_wr_addr : in std_logic_vector(bit_width(inst_depth)-1 downto 0);
        inst_data_in : in std_logic_vector(inst_data_width-1 downto 0);
        data rd1 out inst : out std logic vector(inst data width-1 downto 0);
        data_rd2_out_inst : out std_logic_vector(inst_data_width-1 downto 0)
       );
end DW_ram_2r_w_s_lat_inst;
architecture inst of DW_ram_2r_w_s_lat_inst is
begin
  -- Instance of DW_ram_2r_w_s_lat
  U1 : DW ram 2r w s lat
    generic map ( data width => inst data width, depth => inst depth )
    port map (clk => inst_clk, cs_n => inst_cs_n, wr_n => inst_wr_n,
              rd1_addr => inst_rd1_addr,
                                           rd2 addr => inst rd2 addr,
              wr addr => inst wr addr,
                                         data in => inst data in,
              data_rd1_out => data_rd1_out_inst,
              data_rd2_out => data_rd2_out_inst );
end inst:
-- pragma translate_off
configuration DW_ram_2r_w_s_lat_inst_cfg_inst of DW_ram_2r_w_s_lat_inst is
  for inst
  end for; -- inst
end DW_ram_2r_w_s_lat_inst_cfg_inst;
-- pragma translate_on
```

HDL Usage Through Component Instantiation - Verilog

```
module DW_ram_2r_w_s_lat_inst(inst_clk, inst_cs_n, inst_wr_n, inst_rd1_addr,
                              inst rd2 addr, inst wr addr, inst data in,
                              data_rd1_out_inst, data_rd2_out_inst );
  parameter data width = 8;
  parameter depth = 8;
  `define bit_width_depth 3 // ceil(log2(depth))
  input inst_clk;
  input inst_cs_n;
  input inst_wr_n;
  input [`bit_width_depth-1 : 0] inst_rd1_addr;
  input [`bit_width_depth-1 : 0] inst_rd2_addr;
  input [`bit_width_depth-1 : 0] inst_wr_addr;
  input [data_width-1 : 0] inst_data_in;
  output [data_width-1 : 0] data_rd1_out_inst;
  output [data_width-1 : 0] data_rd2_out_inst;
  // Instance of DW_ram_2r_w_s_lat
  DW_ram_2r_w_s_lat #(data_width, depth)
    U1 (.clk(inst_clk),
                         .cs_n(inst_cs_n),
                                               .wr_n(inst_wr_n),
        .rd1_addr(inst_rd1_addr),
                                    .rd2_addr(inst_rd2_addr),
        .wr_addr(inst_wr_addr),
                                 .data_in(inst_data_in),
        .data rd1 out (data rd1 out inst),
         .data_rd2_out(data_rd2_out_inst) );
endmodule
```

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